

SCRs

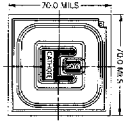
1.6 Amp, Planar

[查询"2N2325AS"供应商](#)

2N2323-2N2329, J, JTX, JTXV
2N2323A-2N2328A, J, JTX, JTXV
2N2323S-2N2329S, J, JTX, JTXV
2N2323AS-2N2328AS, J, JTX, JTXV

FEATURES

- Available as JAN, JANTX, & JANTXV Types
- JAN Types Available in TO-5
- 1.6A D.C. Current
- Peak Currents: to 30A
- Voltage Ratings: to 400V
- 20μA Max. Trigger Current ("A" types)
- 0.6V Max. Trigger Voltage ("A" types)



BACKSIDE ANODE
CHIP THICKNESS
METALLIZATION
TOP BACK

DESCRIPTION

These are premium thyristor switches intended for use in high performance industrial, military and space applications requiring a high degree of reliability assurance. This series is useful in a wide variety of applications including timing and programming circuits, protective and warning circuits, driving relays, driving indicator lamps, encoding and decoding circuits, replacing relays, thyatrons, and magamps, servo motor control, pulse generation, plus many others. The high surge current rating (15A - 1 cycle) makes this series particularly useful for squib firing.

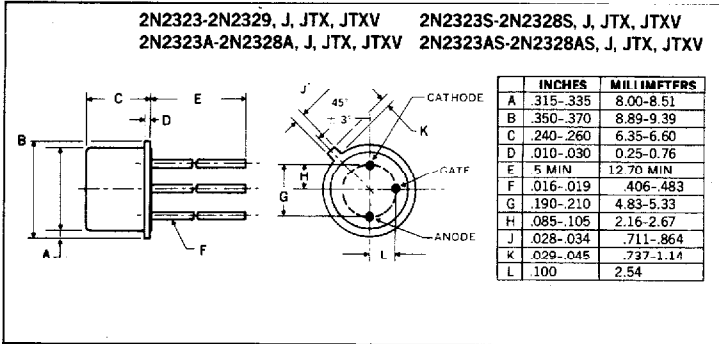
The following JAN, JANTX and JANTXV types are specified under Mil-S-19500/276A and are included in Mil-STD-701 as recommended types for military usage:

2N2323 JAN2N2323S JANTX2N2323S JANTXV2N2323S	2N2324 JAN2N2324S JANTX2N2324S JANTXV2N2324S	2N2325 JAN2N2325S JANTX2N2325S JANTXV2N2325S	2N2326 JAN2N2326S JANTX2N2326S JANTXV2N2326S	2N2327 JAN2N2327S JANTX2N2327S JANTXV2N2327S	2N2328 JAN2N2328S JANTX2N2328S JANTXV2N2328S	2N2329 JAN2N2329S JANTX2N2329S JANTXV2N2329S
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ABSOLUTE MAXIMUM RATINGS

Repetitive Peak Off-State Voltage, V_{DRM}	50V	100V	150V	200V	250V	300V	400V
Repetitive Peak Reverse Voltage, V_{RRM}	50V	100V	150V	200V	250V	300V	400V
Non-Repetitive Peak Reverse Voltage, V_{RSM} (< 5ms)	75V	150V	225V	300V	350V	400V	500V
D.C. On-State Current, I_T							
80°C Ambient							300mA
85°C Case							1.6A
One Cycle Surge (Non-Rep.) On-State Current, I_{TSM}							15A
Repetitive Peak On-State Current, I_{TM}							30A
Gate Power Dissipation, P_{GM}							0.1W
Gate Power Dissipation, $P_{GM(AV)}$							0.01W
Peak Gate Current, I_{GM}							100mA
Reverse Gate Voltage							6V
Reverse Gate Current, I_{GR}							3mA
Storage Temperature Range							-65°C to +150°C
Operating Temperature Range							-65°C to +125°C

MECHANICAL SPECIFICATIONS



TO-205AD (TO-39)



Microsemi Corp.
Watertown
The diode experts

ELECTRICAL SPECIFICATIONS

Test	Symbol	Min.	Typical	Max.	Units	Test Conditions
Visual and Mechanical						MIL-STD-750, Method 2071
25°C						
Off-State Current	I_{DRM}	—	0.1	10	μA	$V_{DRM} = \text{Rating}, R_{GK} = 1K (2K \text{ for "A" Types})$
Reverse Current	I_{RRM}	—	0.1	10	μA	$V_{RRM} = \text{Rating}, R_{GK} = 1K (2K \text{ for "A" Types})$
Gate Trigger Current	I_{GT}	—	2	20	μA	$V_D = 6V, R_L = 100\Omega$
“A” Types		—	50	200	μA	$V_D = 6V, R_L = 100\Omega$
non-“A” Types						
Gate Trigger Voltage	V_{GT}	0.35	0.52	0.60	V	$V_D = 6V, R_{GK} = 2K, R_L = 100\Omega$
“A” Types		0.35	0.55	0.80	V	$V_D = 6V, R_{GK} = 1K, R_L = 100\Omega$
non-“A” Types						
On-State Voltage	V_{TM}	—	2.0	2.2	V	$I_{TM} = 4A (pulse \text{ test})$
Holding Current	I_H	—	0.3	2.0	mA	$V_D = 6V, R_{GK} = 1K (2K \text{ for "A" Types})$
Reverse Gate Current	I_{GR}	—	1	200*	μA	$V_{GR} = 6V$
Delay Time	t_d	—	0.6	—	μs	$I_G = 10mA, I_T = 1A, V_D = 30V$
Rise Time	t_r	—	0.4	—	μs	$I_G = 10mA, I_T = 1A, V_D = 30V$
Circuit Commutated Turn-Off Time	t_q	—	20	—	μs	$I_T = 1A, I_R = 1A, R_{GK} = 1K$
125°C						
Off-State Current	I_{DRM}	—	1	100	μA	$V_{DRM} = \text{Rating}, R_{GK} = 1K (2K \text{ for "A" Types})$
Reverse Current	I_{RRM}	—	1	100	μA	$V_{RRM} = \text{Rating}, R_{GK} = 1K (2K \text{ for "A" Types})$
Gate Trigger Voltage	V_{GT}	0.1	0.3	—	V	$V_D = \text{Rated } V_D, R_{GK} = 1K (2K \text{ for "A" Types})$
Holding Current	I_H	0.1†	—	—	mA	$V_D = 6V, R_{GK} = 2K$
“A” Types		0.15†	—	—	mA	$V_D = 6V, R_{GK} = 1K$
non-“A” Types						
Off-State Voltage — Critical Rate of Rise	dv/dt	0.7*	—	—	V/ μs	$V_D = \text{Rating}, R_{GK} = 2K$
“A” Types		1.8*	—	—	V/ μs	$V_D = \text{Rating}, R_{GK} = 1K$
non-“A” Types						
—65°C						
Off-State Current	I_{DRM}	—	.05	5.0*	μA	$V_{DRM} = \text{Rating}, R_{GK} = 1K (2K \text{ for "A" Types})$
Reverse Current	I_{RRM}	—	.05	5.0*	μA	$V_{RRM} = \text{Rating}, R_{GK} = 1K (2K \text{ for "A" Types})$
Gate Trigger Current	I_{GT}	—	50	75	μA	$V_D = 6V, R_L = 100\Omega$
“A” Types		—	100	350	μA	$V_D = 6V, R_L = 100\Omega$
non-“A” Types						
Gate Trigger Voltage	V_{GT}	—	0.7	0.8*	V	$V_D = 6V, R_{GK} = 2K, R_L = 100\Omega$
“A” Types		—	—	0.9†	V	$V_D = 6V, R_{GK} = 2K, R_L = 100\Omega$
non-“A” Types		—	0.75	1.0	V	$V_D = 6V, R_{GK} = 1K, R_L = 100\Omega$
Holding Current	I_H	—	—	3.0†	mA	$V_D = 6V, R_{GK} = 1K (2K \text{ for "A" Types})$

* JAN and JANTX Types only.
† Industrial Types only.

JAN and JANTX Acceptance Tests

100% Screening TX-Types

Group B Tests

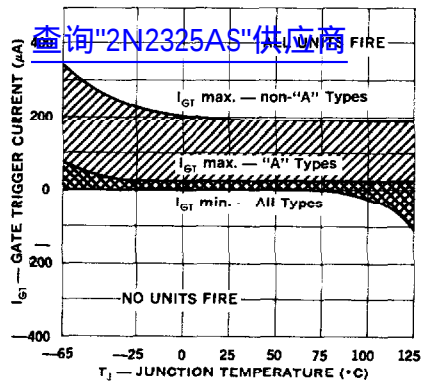
Group C Tests

High Temperature Storage
Temperature Cycling
Constant Acceleration
Fine & Gross Hermetic Seal
Electrical Test
Burn-in
Electrical Test

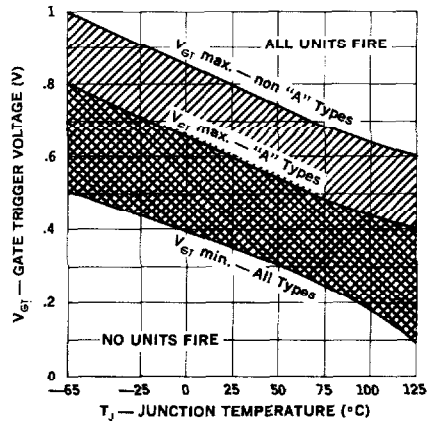
Subgroup 1 — Reverse Gate Current
Surge Current
Non-Repetitive Reverse Voltage
Subgroup 2 — Low Temp. Reverse Blocking Current
Low Temp. Forward Blocking Current
Low Temp. Gate Trigger Voltage
Low Temp. Gate Trigger Current
Subgroup 3 — Temperature Cycling
Thermal Shock
Moisture Resistance
Solderability
Subgroup 4 — Blocking Life Test

Subgroup 1 — Physical Dimensions
Subgroup 2 — Shock
Constant Acceleration
Vibration, Variable Frequency
Subgroup 3 — Barometric Pressure, Reduced
Subgroup 4 — Salt Atmosphere
Subgroup 5 — Terminal Strength
Subgroup 6 — Intermittent Operating Life Test

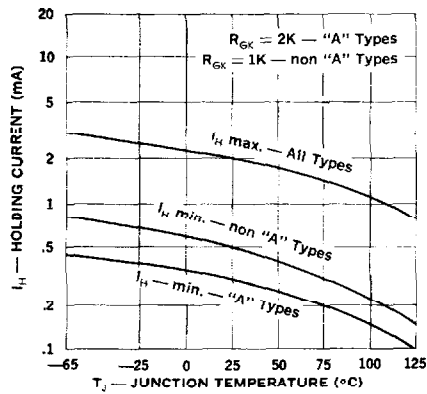
Gate Trigger Current



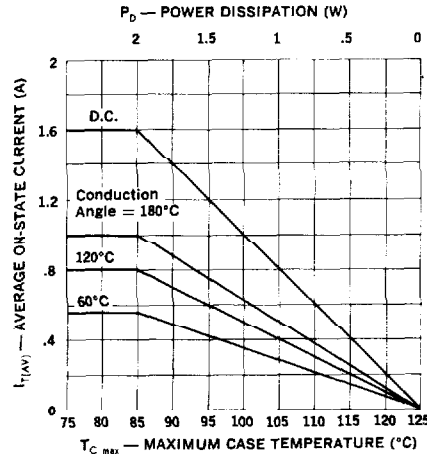
Gate Trigger Voltage



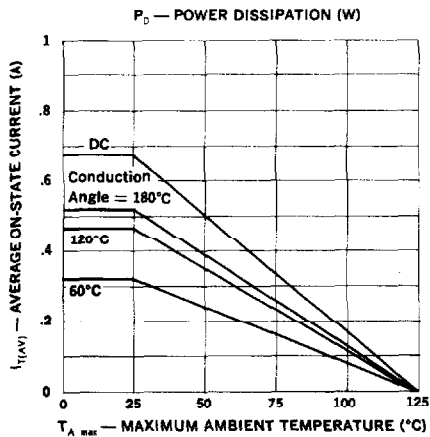
Holding Current



Average Current vs. Case Temperature



Average Current vs. Ambient Temperature



Surge Current

